

Please replace the paragraph beginning at line 11 of page 7, with the following rewritten paragraph:

A2 --In operation, a first wafer W_1 is loaded (e.g., via a wafer handler that is not shown) onto load cup 60 and mounted therefrom to first wafer mounting head 29a. Rotatable cross bar 62 is indexed carrying the first wafer W_1 to the first polishing station 52₁ where wafer W_1 is to be polished, while a second wafer W_2 is loaded onto load cup 60 and mounted therefrom to the second wafer mounting head 29b. The rotatable cross bar 62 is indexed again; the wafer W_1 is polished by the second polishing station 52₂ (e.g., with a different polishing fluid than that used by the first polishing station 52₁); the second wafer W_2 is polished by the first polishing station 52₁ and a third wafer W_3 is loaded to the load cup 60 and mounted to the third wafer mounting head 29c.--

Please replace the paragraph beginning at line 21 of page 7, with the following rewritten paragraph:

A3 --Thereafter, rotatable cross bar 62 indexes and the first wafer W_1 is carried to polishing station 52₃. Meanwhile, the second wafer W_2 is polished by second polishing station 52₂; the third wafer W_3 is polished by first polishing station 52₁ and a fourth wafer W_4 is loaded onto load cup 60 and mounted to a fourth wafer mounting head 29d.--

Please replace the paragraph beginning at line 26 of page 7, with the following rewritten paragraph:

A4 --The rotatable cross bar 62 then indexes carrying the first wafer W_1 to load cup 60 where the first wafer mounting head 29a places the first wafer W_1 on the load cup 60 and a wafer handler (not shown) extracts the first wafer W_1 from the system 38.--

IN THE CLAIMS:

Please amend claims 1 and 7 as follows.

A5 5/15/01
1. (Amended) A multistep method of polishing a semiconductor substrate with a polishing fluid to remove a selected amount of material from said substrate, said method comprising: